

# BLF182XR; BLF182XRS

Power LDMOS transistor

Rev. 1 — 23 July 2015

Objective data sheet

## 1. Product profile

### 1.1 General description

A 250 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. Application information

Test signal	f (MHz)	V <sub>DS</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	η <sub>D</sub> (%)
pulsed RF	108	50	250	28	72

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

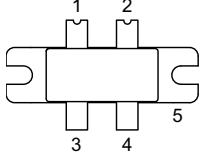
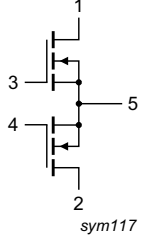
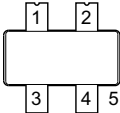
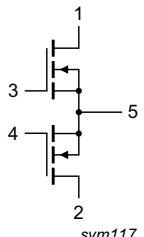
### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
<b>BLF182XR (SOT1121A)</b>			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source <a href="#">[1]</a>		
<b>BLF182XRS (SOT1121B)</b>			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source <a href="#">[1]</a>		

[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF182XR	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A
BLF182XRS	-	earless flanged ceramic package; 4 leads	SOT1121B

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	135	V
$V_{GS}$	gate-source voltage		-6	+11	V
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature	<a href="#">[1]</a>	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_j = 115\text{ °C}$ [1][2]	<tdb>	K/W
$Z_{th(j-c)}$	transient thermal impedance from junction to case	$T_j = 150\text{ °C}$ ; $t_p = 100\text{ }\mu\text{s}$ ; $\delta = 20\%$ [3]	<tdb>	K/W

[1]  $T_j$  is the junction temperature.

[2]  $R_{th(j-c)}$  is measured under RF conditions.

[3] See <tdb>.

## 6. Characteristics

**Table 6. DC characteristics**

$T_j = 25\text{ °C}$ ; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ ; $I_D = 1.0\text{ mA}$	135	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$ ; $I_D = 100\text{ mA}$	1.25	1.8	2.25	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50\text{ V}$ ; $I_D = 50\text{ mA}$	-	1.6	-	V
$I_{DSS}$	drain leakage current	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$	-	-	1.4	$\mu\text{A}$
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$ ; $V_{DS} = 10\text{ V}$	-	14.3	-	A
$I_{GSS}$	gate leakage current	$V_{GS} = 11\text{ V}$ ; $V_{DS} = 0\text{ V}$	-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$ ; $I_D = 3.5\text{ A}$	-	0.43	-	$\Omega$

**Table 7. AC characteristics**

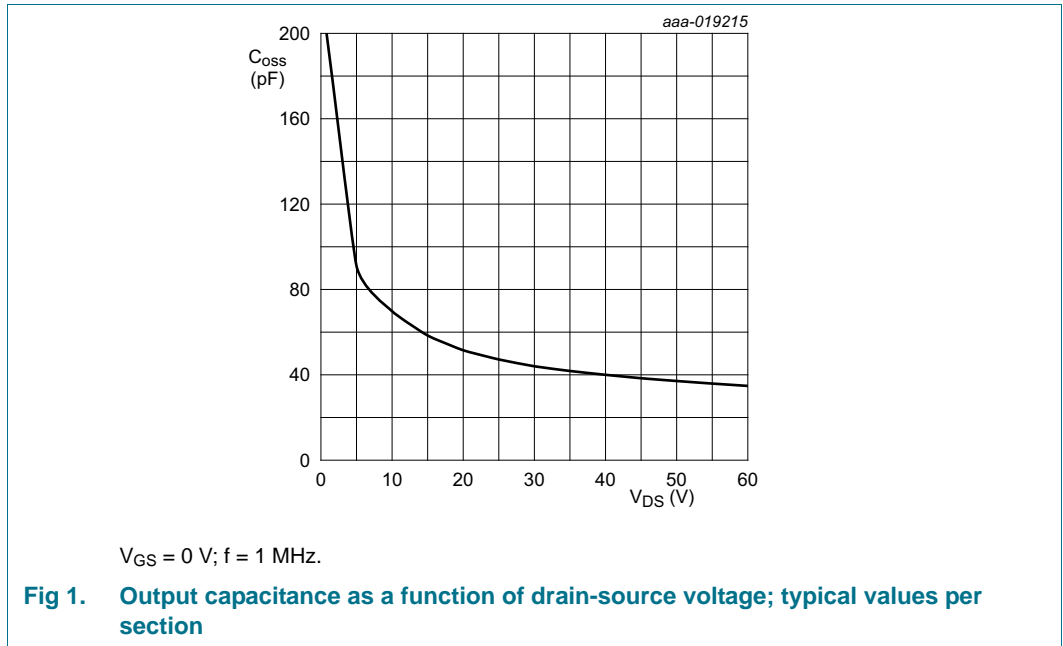
$T_j = 25\text{ °C}$ ; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{rs}$	feedback capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; $f = 1\text{ MHz}$	-	0.7	-	pF
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; $f = 1\text{ MHz}$	-	116	-	pF
$C_{oss}$	output capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 50\text{ V}$ ; $f = 1\text{ MHz}$	-	37	-	pF

**Table 8. RF characteristics**

Test signal: pulsed RF;  $t_p = 100\text{ }\mu\text{s}$ ;  $\delta = 20\%$ ;  $f = 108\text{ MHz}$ ; RF performance at  $V_{DS} = 50\text{ V}$ ;  $I_{Dq} = 100\text{ mA}$ ;  $T_{case} = 25\text{ °C}$ ; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_p$	power gain	$P_L = 250\text{ W}$	<tdb>	28	-	dB
$RL_{in}$	input return loss	$P_L = 250\text{ W}$	-	-10	-	dB
$\eta_D$	drain efficiency	$P_L = 250\text{ W}$	<tdb>	72	-	%

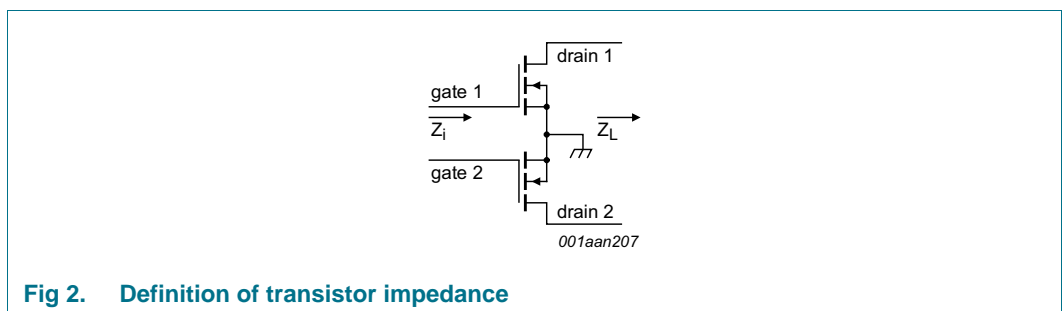


## 7. Test information

### 7.1 Ruggedness in class-AB operation

The BLF182XR and BLF182XRS are capable of withstanding a load mismatch corresponding to  $V_{SWR} > 65 : 1$  through all phases under the following conditions:  $V_{DS} = 50\text{ V}; I_{Dq} = 100\text{ mA}; P_L = 250\text{ W}$  pulsed;  $f = 108\text{ MHz}$ .

### 7.2 Impedance information



**Table 9. Typical push-pull impedance**

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50\text{ V}$  and  $P_L = 250\text{ W}$ .

f (MHz)	$Z_i$ ( $\Omega$ )	$Z_L$ ( $\Omega$ )
108	<td>	<td>

### 7.3 UIS avalanche energy

**Table 10. Typical avalanche data per section**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ ; typical test data; test jig without water cooling.

$I_{AS}$ (A)	$E_{AS}$ (J)
<td>	<td>
<td>	<td>
<td>	<td>

For information see application note *AN10273*.

8. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 4 leads

SOT1121A

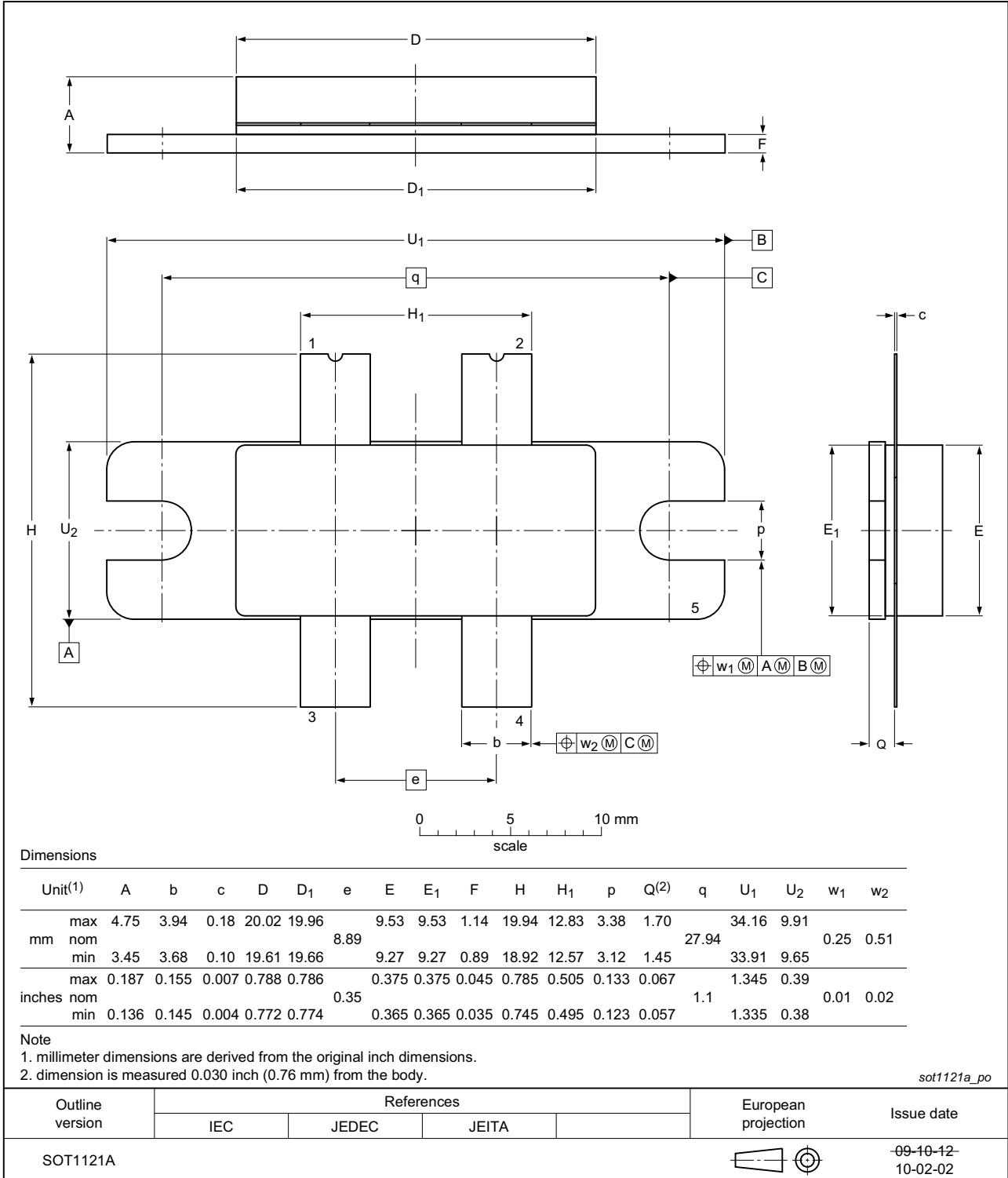


Fig 3. Package outline SOT1121A

Earless flanged ceramic package; 4 leads

SOT1121B

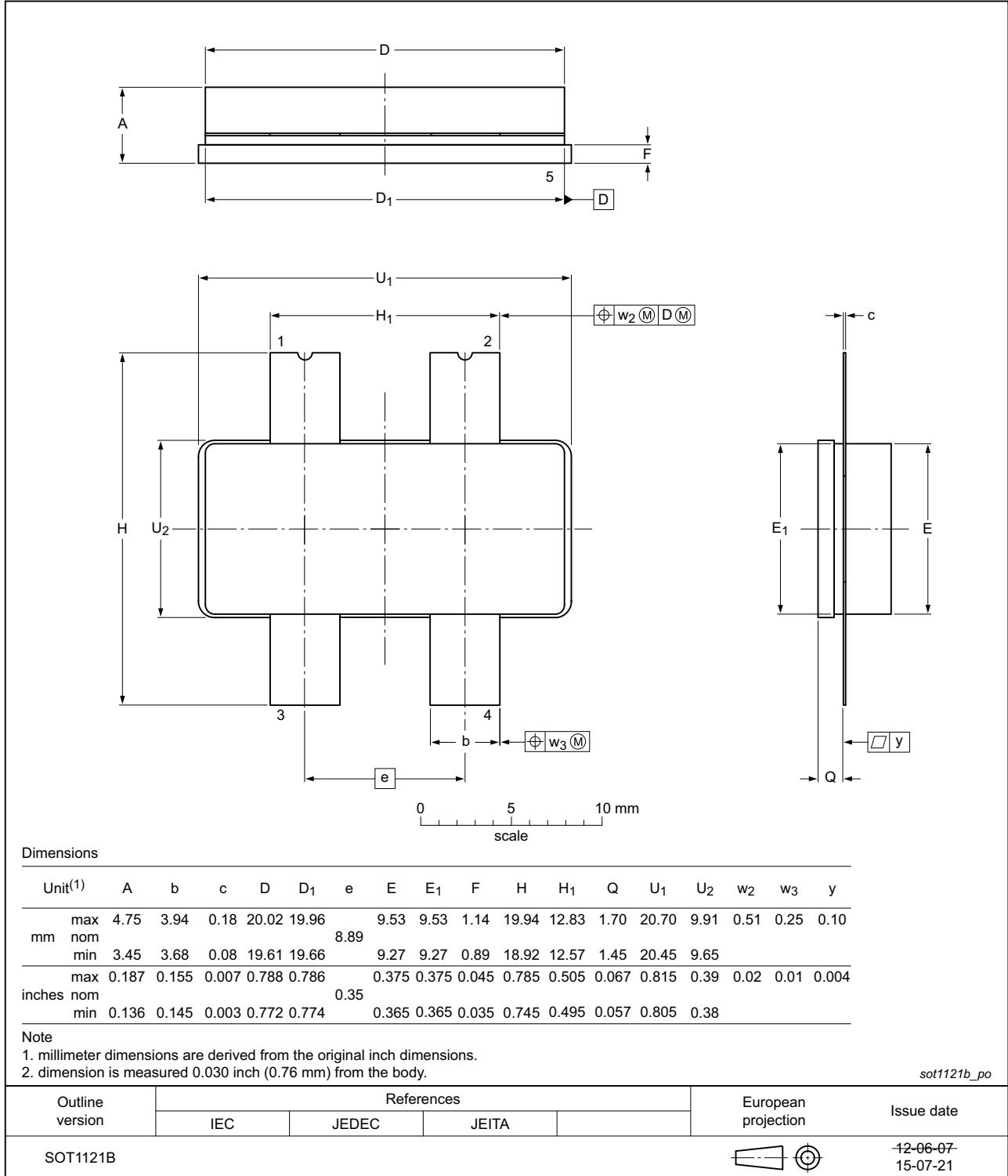


Fig 4. Package outline SOT1121B

## 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

## 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF182XR_BLF182XRS v.1	20150723	Objective data sheet	-	-



## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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